TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP281,TLP281-4

PROGRAMMABLE CONTROLLERS

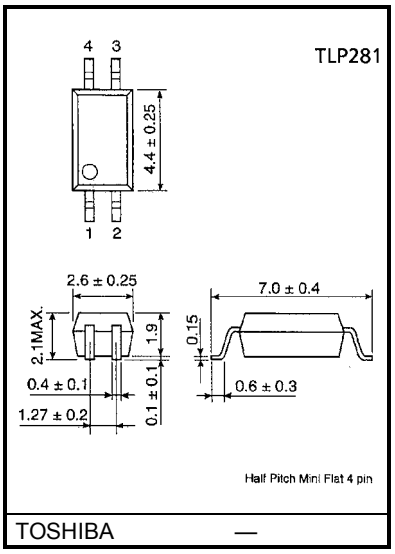
AC/DC-INPUT MODULE

PC CARD MODEM(PCMCIA)

TLP281 and TLP281-4 is a very small and thin coupler,suitable for surface mount assembly in applications such as PCMCIA Fax modem,programmable controllers.
TLP281 and TLP281-4 consist of photo transistor,optically coupled to a gallium arsenide infrared emitting diode.

- Collector-Emitter Voltage : 80 V (MIN)
- Current Transfer Ratio : 50% (MIN)
  Rank GB : 100% (MIN)
- Isolation Voltage : 2500 Vrms (MIN)
- UL Recognized : UL1577 , File No. E67349
- BSI Approved : BS EN 60065: 1994,
  : BS EN 41003: 1997
  Certificate No. 8143, 8144

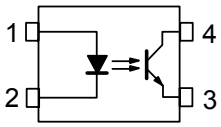
Unit in mm



Weight: 0.05 g

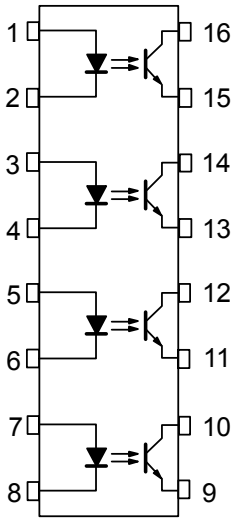
PIN CONFIGURATION(Top view)

TLP281



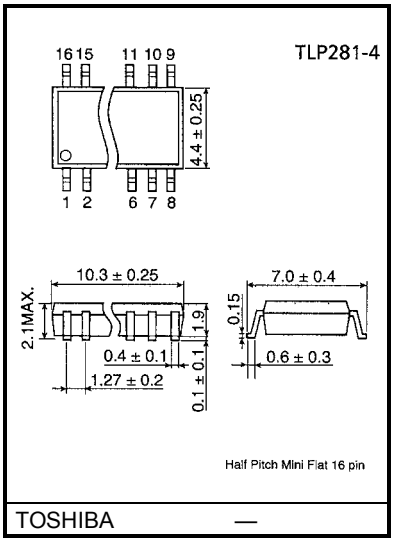
1:ANODE
2:CATHODE
3:EMITTER
4:COLLECTOR

TLP281-4



1,3,5,7 :ANODE
2,4,6,8 :CATHODE
9,11,13,15 :EMITTER
10,12,14,16 :COLLECTOR

Unit in mm



Weight: 0.19 g

TYPE	Classi-Fication(*1)	Current Transfer Ration (%) (I_C / I_F) I_F = 5 mA, V_{CE} = 5 V, Ta = 25℃		Marking of Classification
		Min	Max	
TLP281	Blank	50	600	Blank ,Y■,YE,G,G■,GR,B,BL,GB
	Rank Y	50	150	YE
	Rank GR	100	300	GR
	Rank BL	200	600	BL
	Rank GB	100	600	GB
	Rank YH	75	150	Y■
	Rank GRL	100	200	G
	Rank GRH	150	300	G■
	Rank BLL	200	400	B
TLP281-4	Blank	50	600	Blank , GB
	Rank GB	100	600	GB

*1: Ex. rank GB: TLP281 (GB)

(Note): Application type name for certification test, please use standard product type name, i.e.
TLP281 (GB): TLP281−1 , TLP281−4 (GB): TLP281−4

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING		UNIT
			TLP281	TLP281−4	
LED	Forward Current	I_F	50		mA
	Forward Current Derating	ΔI_F /°C	−0.7 (Ta≥53°C)	−0.5 (Ta≥25°C)	mA /°C
	Pulse Forward Current	I_{FP}	1		A
	Reverse Voltage	V_R	5		V
	Junction Temperature	T_j	125		°C
DETECTOR	Collector-Emitter Voltage	V_{CEO}	80		V
	Emitter-Collector Voltage	V_{ECO}	7		V
	Collector Current	I_C	50		mA
	Collector Power Dissipation (1 Circuit)	P_C	150	100	mW
	Collector Power Dissipation Derating(Ta≥25°C) (1 Circuit)	ΔP_C /°C	−1.5	−1.0	mW /°C
	Junction Temperature	T_j	125		°C
Operating Temperature Range		T_{opr}	−55~100		°C
Storage Temperature Range		T_{stg}	−55~125		°C
Lead Soldering Temperature		T_{sol}	260 (10s)		°C
Total Package Power Dissipation (1 Circuit)		P_T	200	170	mW
Total Package Power Dissipation Derating (Ta≥25°C) (1 Circuit)		ΔP_T /°C	−2.0	−1.7	mW /°C
Isolation Voltage (Note1)		BV_S	2500(AC,1min,R.H.≤60%)		Vrms

(Note1)Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	I_F = 10 mA	1.0	1.15	1.3	V
	Reverse Current	I_R	V_R = 5 V	—	—	10	μA
	Capacitance	C_T	V = 0, f = 1 MHz	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)\ CEO}$	I_C = 0.5 mA	80	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)\ ECO}$	I_E = 0.1 mA	7	—	—	V
	Collector Dark Current (Note2)	I_{CEO}	V_{CE} = 48 V, Ambient Light Below (100 ℓx)	—	0.01 (2)	0.1 (10)	μA
			V_{CE} = 48 V, Ta = 85°C Ambient Light Below (100 ℓx)	—	2 (4)	50 (50)	μA
	Capacitance (Collector to Emitter)	C_{CE}	V = 0, f = 1 MHz	—	10	—	pF

(Note 2) Because of the construction,leak current might be increased by ambient light. Please use photocoupler with less ambient light.

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_C / I_F	I_F = 5 mA, V_{CE} = 5 V	50	—	600	%
		Rank GB	100	—	600	
Saturated CTR	I_C / $I_{F\ (sat)}$	IF = 1 mA, VCE = 0.4 V	—	60	—	%
		Rank GB	30	—	—	
Collector-Emitter Saturation Voltage	$V_{CE\ (sat)}$	I_C = 2.4 mA, I_F = 8 mA	—	—	0.4	V
		I_C = 0.2 mA, I_F = 1 mA	—	0.2	—	
		Rank GB	—	—	0.4	
Off-State Collector Current	$I_{C\ (off)}$	V_F = 0.7 V, V_{CE} = 48 V	—	—	10	μA

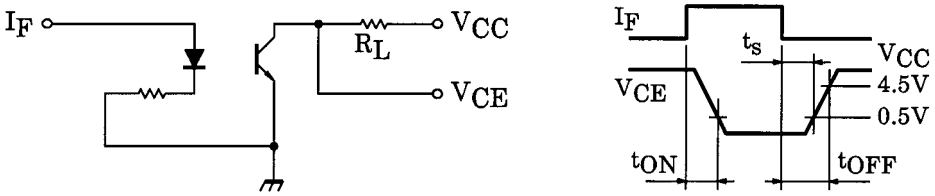
ISOLATION CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	C_S	V_S = 0 V, f = 1 MHz	—	0.8	—	pF
Isolation Resistance	R_S	V_S = 500 V, R.H.≤60%	5×10^{10}	10^{14}	—	Ω
Isolation Voltage	BV_S	AC , 1 minute	2500	—	—	Vrms
		AC , 1 second,in OIL	—	5000	—	
		DC , 1 minute, in OIL	—	5000	—	Vdc

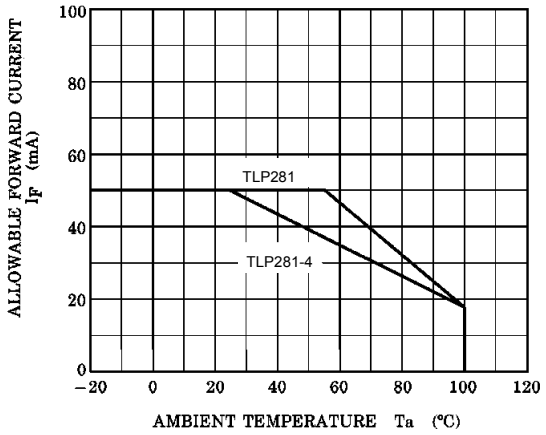
SWITCHING CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t_r	V_{CC} = 10 V, I_C = 2 mA R_L = 100Ω	—	2	—	μs
Fall Time	t_f		—	3	—	
Turn-On Time	t_{on}		—	3	—	
Turn-Off Time	t_{off}		—	3	—	
Turn-On Time	t_{ON}	R_L = 1.9 kΩ (Fig.1) V_{CC} = 5 V, I_F = 16 mA	—	2	—	μs
Storage Time	t_s		—	25	—	
Turn-Off Time	t_{OFF}		—	40	—	

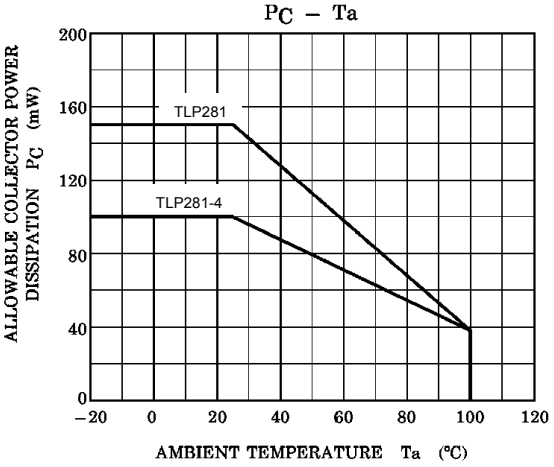
(Fig.1)SWITCHING TIME TEST CIRCUIT



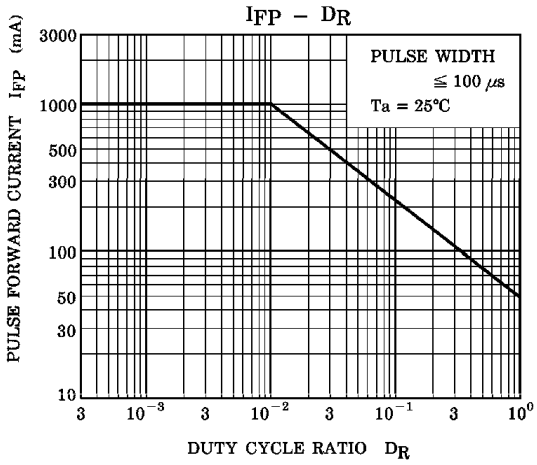
I_F – Ta



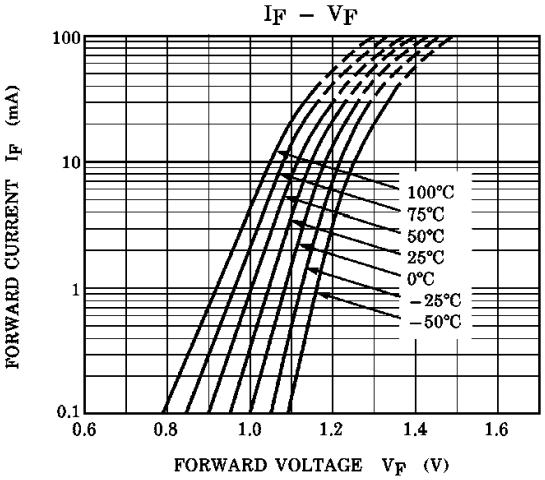
P_C – Ta



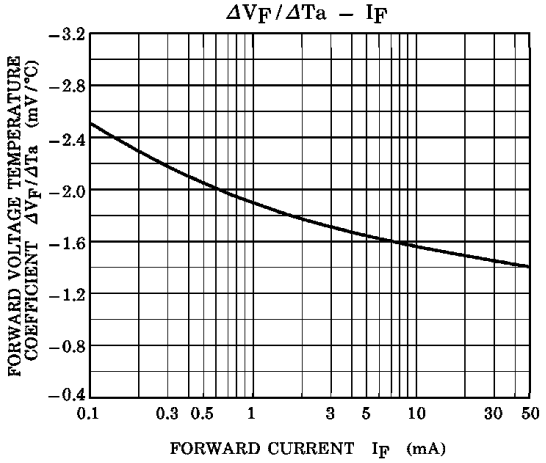
I_{FP} – D_R



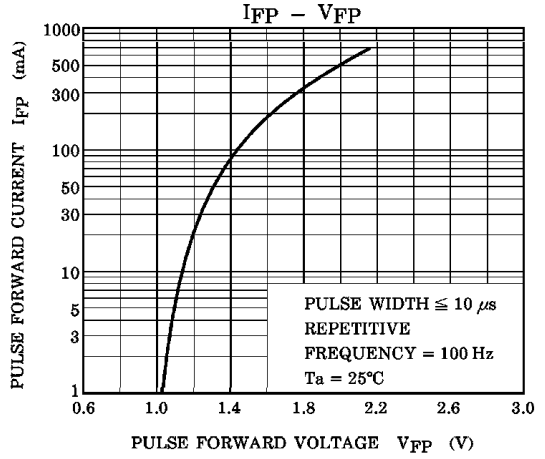
I_F – V_F



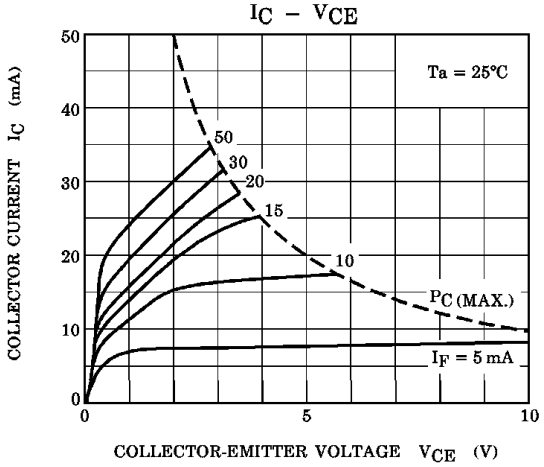
$\Delta V_F / \Delta Ta$ – I_F



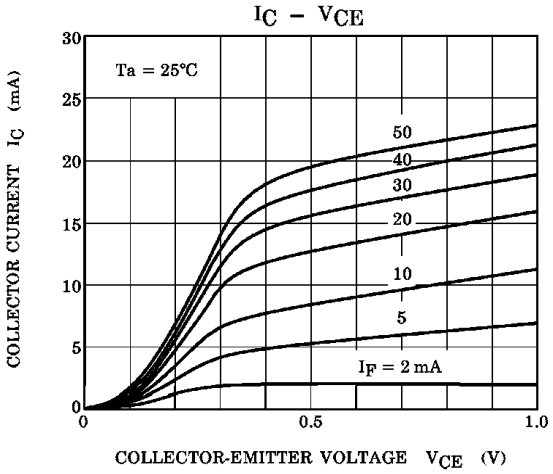
I_{FP} – V_{FP}



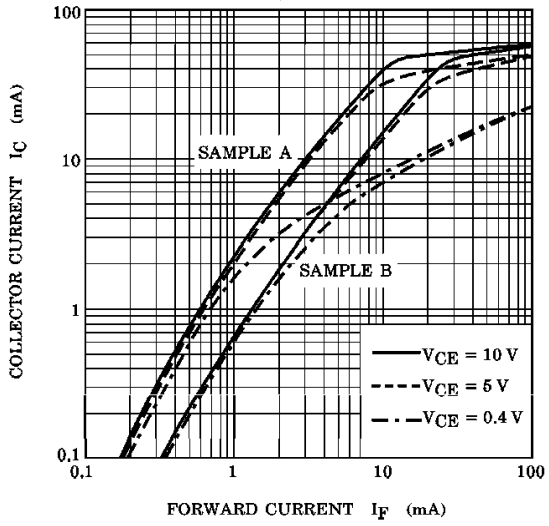
$I_C - V_{CE}$



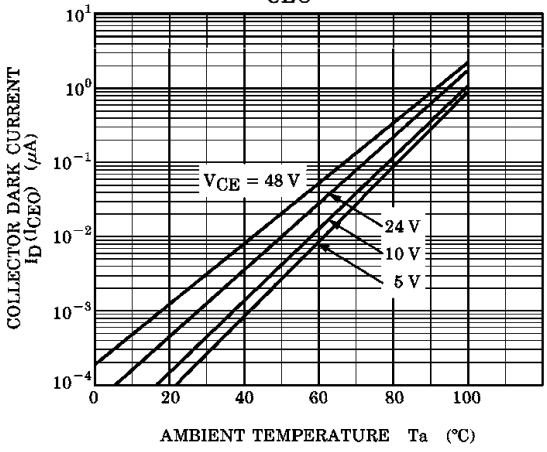
$I_C - V_{CE}$



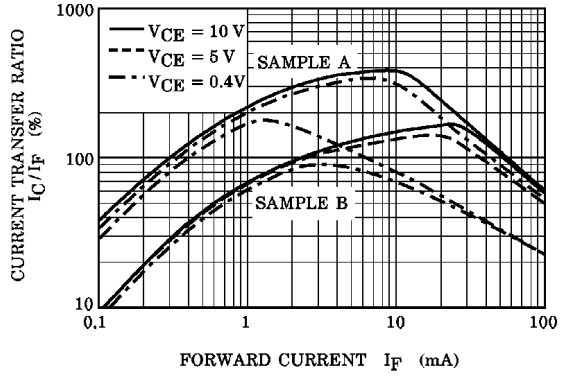
$I_C - I_F$



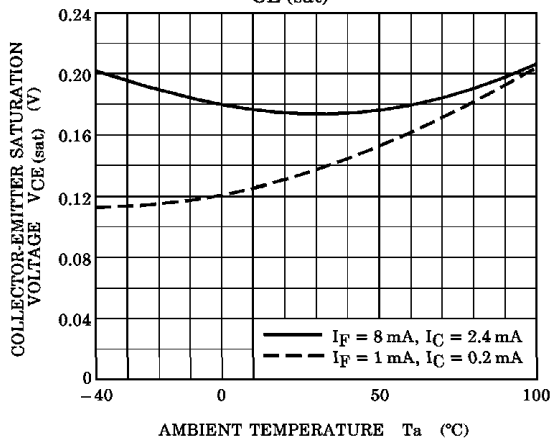
$I_{CEO} - Ta$



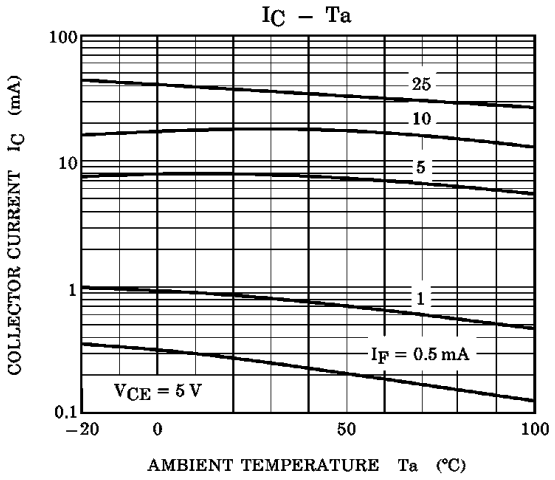
$I_C / I_F - I_F$



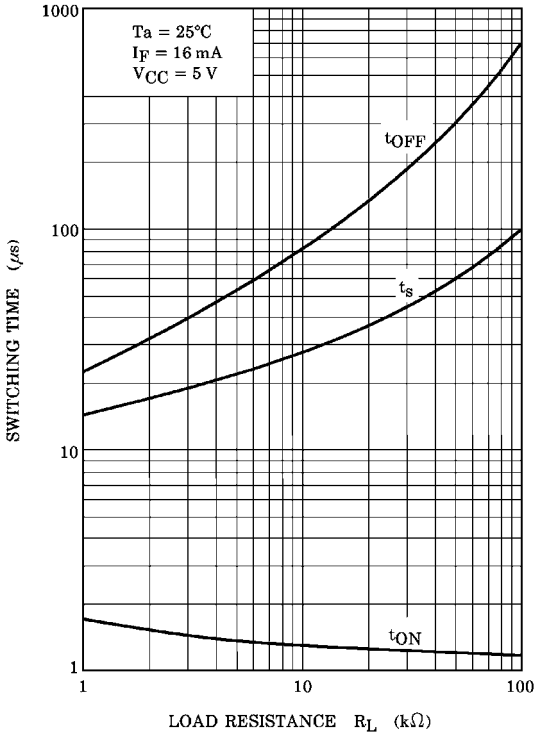
V_{CE} (sat) – Ta



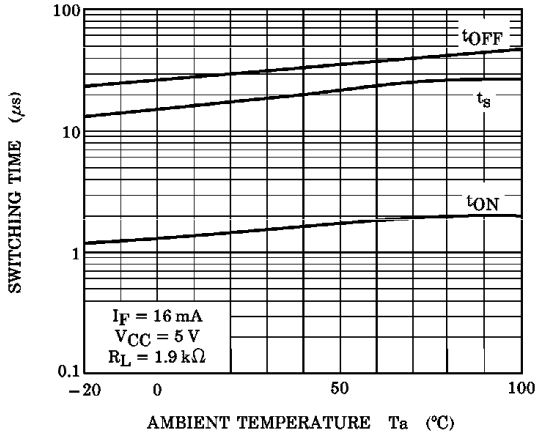
I_C – Ta



SWITCHING TIME – R_L



SWITCHING TIME – Ta



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